



PATENT APPLICATION

Sheet 1 of 5

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200210175-1	APPLICATION NO. 10/619639	CONFIRMATION NO.
	APPLICANT Martha A. Truninger et al.		
	FILING DATE Herewith 7/15/2003	GROUP Unkn. 2853	

REFERENCE DESIGNATION

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EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	1A	5,385,635	01/1995	O'Neill	_____
	1B	5,387,314	02/1995	Baughman et al.	_____
	1C	5,393,711	02/1995	Biallas et al.	_____
	1D	5,441,593	08/1995	Baughman et al.	_____
	1E	5,498,312	03/1996	Laermer et al.	_____
	1F	5,501,893	03/1996	Laermer et al.	_____
	1G	5,526,454	06/1996	Mayer	_____
	1H	5,541,140	07/1998	Goebel et al.	_____
	1I	5,716,533	02/1998	O'Neill et al.	_____
		1J	5,756,901	05/1998	Kurle et al.
1K		5,870,123	02/1999	Lorenze, Jr. et al.	_____

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		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	1L	WO 9837577	08/1998	Bosch GMBH	—	
	1M	WO 0023376	04/2000	Bosch GMBH	—	
	1N	EP 0865151A2	09/1998	Hewlett-Packard Co.	—	
	1O	EP 0886307A2	12/1998	Canon Kabushiki	—	
	1P	EP 0978832A2	02/2000	Hewlett-Packard Co.	—	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	1Q	"Cryogenic Etching of Deep Narrow Trenches In Silicon"; by: Aachboun et al.; Journal Of Vacuum Science & Technology A; Vol. 18, No. 4; pt. 1-2; July-Aug. 2000; Abstract Only.
	1R	"An Array of Hollow Microcapillaries For The Controlled Injection of Genetic Materials Into Animal/Plant Cells"; by: K. Chun et al.; Proceedings of 12th International Workshop on Micro Electro Mechanical Systems (MEMS); Jan. 1999; Abstract Only.
	1S	"Deep Etching Key to the MEMS/MST Revolution"; by: Prashant Gadil; R & D; July 1998; p. 38.

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DATE CONSIDERED



PATENT APPLICATION

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

FORM PTO-1449	ATTY. DOCKET NO. 200210175-1	APPLICATION NO. 10/619 639	CONFIRMATION NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT Martha A. Truning r et al.		
(Use several sheets if necessary)	FILING DATE Herewith 7/15/2003	GROUP Unkn.	2853

REFERENCE DESIGNATION




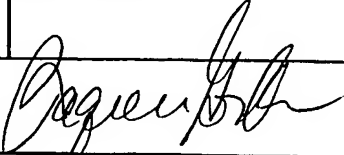
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EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	2A	6,008,138	12/1999	Laermer et al.	—
	2B	6,045,710	04/2000	Silverbrook	—
	2C	6,081,635	06/2000	Hehmann	—
	2D	6,096,656	08/2000	Matzke et al.	—
	2E	6,139,761	10/2000	Ohkuma	—
	2F	6,305,080	10/2001	Komuro et al.	—
	2G	5,124,717	06/1992	Campanelli et al.	—
	2H	5,141,596	08/1992	Hawkins et al.	—
	2I	6,481,832	11/19/2002	Liu et al.	—
	2J				
	2K				

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	2L	DE19538103A1	04/1997	Bosch GMBH	—	
	2M	GB2245366A	01/1992	Bosch GMBH	—	
	2N	GB 2290413A	12/1995	Bosch GMBH	—	
	2O	GB 2341348A	03/2000	Bosch GMBH	—	
	2P					

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	2Q	"Anisotropic Silicon Etch Characterization in the TFTL STS Etcher"; August 20, 1999; pp: 1-5.
	2R	"Etching Characteristics And Profile Control in a Time Multiplexed Inductively Coupled Plasma Etcher"; by: AA Ayon, CC Lin, RA Braff & MA Schmidt of the Department of Electrical Engineering and Computer Science (EECS); Solid-State Sensor and Actuator Workshop, Hilton Head Island, SC; June 8-11, 1998; pp: 41-44.
	2S	"Characterization of a Time Multiplexed Inductively Coupled Plasma Etcher"; by: AA Ayon, R Braff, CC Lin, HH Sawin & MA Schmidt; Journal of the Electrochemical Society; 146 (1); 1999; pp: 339-349.
EXAMINER 	DATE CONSIDERED 2/2005	

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Sheet 3 of 5

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200210175-1

APPLICATION NO.

10/69639

CONFIRMATION NO.

APPLICANT

Martha A. Truninger et al.

FILING DATE

Herewith 7/15/2003

GROUP

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REFERENCE DESIGNATION




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FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	3L				
	3M				
	3N				
	3O				
	3P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	3Q	STS-Surface Technology Systems-1st ASE Users Meeting, pp. 1-10; Advanced Silicon Etch, pp. 1-28; Technology Review, pp. 1-10; California, 1997.
	3R	"High-Aspect-Ratio Si Etching for Microsensor Fabrication"; by: WH Juan & SW Pang; Journal of Vacuum Science & Technology A; Vol. 13, No. 3; 1995; pp. 834-838.
	3S	"Bosch Deep Silicon Etching: Improved Uniformity and Etch Rate for Advanced MEMS Applications"; by: F Laermer et al.; 0-7803-5194-00; 1999; pp. 211-216.

EXAMINER

DATE CONSIDERED

PATENT APPLICATION

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<p>FORM PTO-1449</p> <p>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</p> <p>(Use several sheets if necessary)</p>	<p>ATTY. DOCKET NO. 200210175-1</p>	<p>APPLICATION NO. 10/649639</p>	<p>CONFIRMATION NO.</p>
<p>APPLICANT Martha A. Truninger et al.</p>			
<p>FILING DATE Herewith 7/15/03</p>		<p>GROUP Unkn. 2853</p>	

REFERENCE DESIGNATION




U.S. PATENT DOCUMENTS

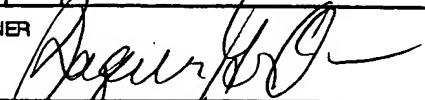
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FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
4L				
4M				
4N				
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	4Q	"Advanced Silicon Etching Using High Density Plasmas"; by: JK Bhardwaj & H Ashraf; SPIE-Society of Photo-Optical Instrumentation Engineers; Vol. 2639; October 1995; pp 224-233.
	4R	"Recent Advances in Silicon Etching for MEMS Using the ASE Process"; by: AM Hynes et al.; Sensors And Actuators; Vol. 74; 1999; pp 13-17.
	4S	"Fabrication of Thick Silicon Dioxide Layers Using DRIE, Oxidation and Trench Refill"; by: C Zhang & K Najafi; Proceedings of 15th IEEE International Conference on Micro Electro Mechanical Systems; Jan. 20-24, 2002; pp. 160-163.

<p>EXAMINER </p>	<p>DATE CONSIDERED 2/2005</p>
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PATENT APPLICATION

Sheet 5 of 5

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200210175-1

APPLICATION NO.

10/69639

CONFIRMATION NO.

APPLICANT

Martha A. Truninger et al.

FILING DATE

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REFERENCE DESIGNATION


U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
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FOREIGN PATENT DOCUMENTS

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	5L				
	5M				
	5N				
	5O				
	5P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	5Q	"Fabrication of Out-of-Plane Curved Surfaces in SI by Utilizing RIE Lag"; by: TA Chou & K Najafi; Proceedings of 15th IEEE International Conference on Micro Electro Mechanical Systems; Jan. 20-24, 2002; pp. 145-148.
	5R	
	5S	

EXAMINER

DATE CONSIDERED

2/2005